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●Electrical characteristics (Ta = 25°C)

| Parameter                               | Symbol        | Min. | Typ. | Max.      | Unit     | Test Conditions             |
|---|---------------|------|------|-----------|----------|-----------------------------|
| Gate-source leakage                     | $I_{GSS}$     | —    | —    | $\pm 100$ | nA       | $V_{GS}=\pm 30V, V_{DS}=0V$ |
| Drain-source breakdown voltage          | $V_{(BR)DSS}$ | 200  | —    | —         | V        | $I_D=1mA, V_{GS}=0V$        |
| Zero gate voltage drain current         | $I_{DSS}$     | —    | —    | 100       | $\mu A$  | $V_{DS}=200V, V_{GS}=0V$    |
| Gate threshold voltage                  | $V_{GS(th)}$  | 2.0  | —    | 4.0       | V        | $V_{DS}=10V, I_D=1mA$       |
| Static drain-source on-state resistance | $R_{DS(on)}$  | —    | 0.7  | 0.9       | $\Omega$ | $I_D=1.5A, V_{GS}=10V$      |
| Forward transfer admittance             | $ Y_{fs} $    | 0.6  | 1.5  | —         | S        | $I_D=1.5A, V_{DS}=10V$      |
| Input capacitance                       | $C_{iss}$     | —    | 230  | —         | pF       | $V_{DS}=10V$                |
| Output capacitance                      | $C_{oss}$     | —    | 100  | —         | pF       | $V_{GS}=0V$                 |
| Reverse transfer capacitance            | $C_{rss}$     | —    | 35   | —         | pF       | $f=1MHz$                    |
| Turn-on delay time                      | $t_{d(on)}$   | —    | 10   | —         | ns       | $I_D=1.5A, V_{DD}=10V$      |
| Rise time                               | $t_r$         | —    | 12   | —         | ns       | $V_{GS}=10V$                |
| Turn-off delay time                     | $t_{d(off)}$  | —    | 26   | —         | ns       | $R_L=68\Omega$              |
| Fall time                               | $t_f$         | —    | 34   | —         | ns       | $R_G=10\Omega$              |
| Reverse recovery time                   | $t_{rr}$      | —    | 96   | —         | ns       | $I_{DR}=3A, V_{GS}=0V$      |
| Reverse recovery charge                 | $Q_{rr}$      | —    | 0.59 | —         | $\mu C$  | $di/dt=100A/\mu s$          |

●Electrical characteristic curves

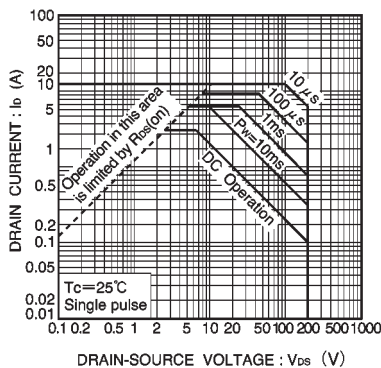


Fig.1 Maximum safe operating area

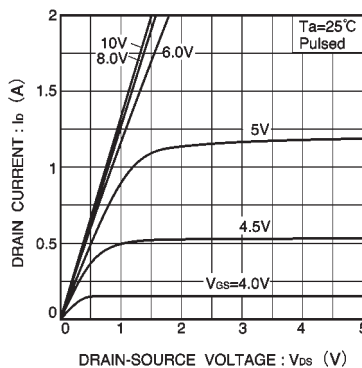


Fig.2 Typical output characteristics

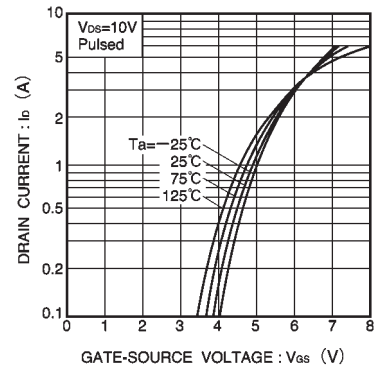


Fig.3 Typical transfer characteristics

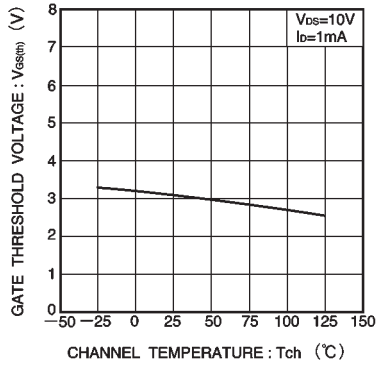


Fig.4 Gate threshold voltage vs. channel temperature

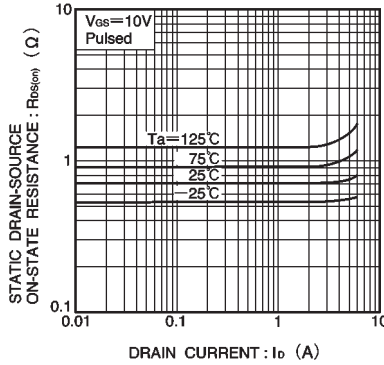


Fig.5 Static drain-source on-state resistance vs. drain current

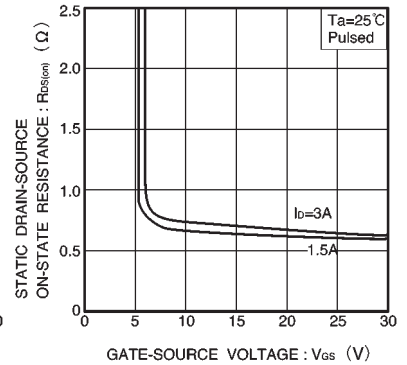


Fig.6 Static drain-source on-state resistance vs. gate-source voltage

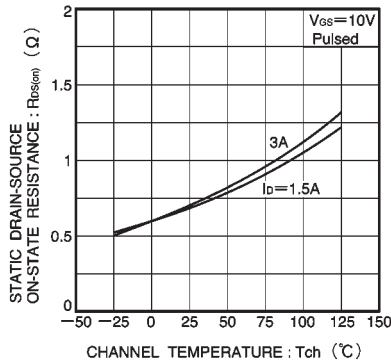


Fig.7 Static drain-source on-state resistance vs. channel temperature

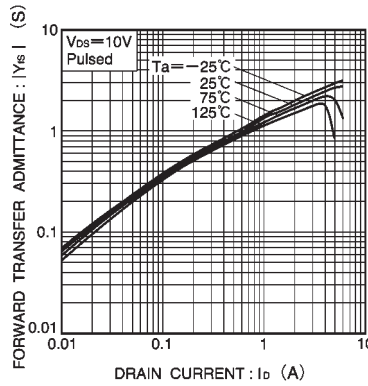


Fig.8 Forward transfer admittance vs. drain current

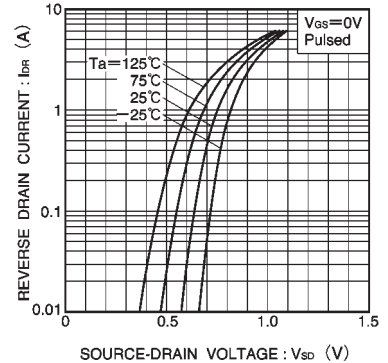


Fig.9 Reverse drain current vs. source-drain voltage ( I )

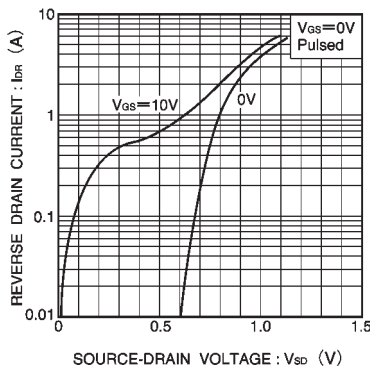


Fig.10 Reverse drain current vs. source-drain voltage ( II )

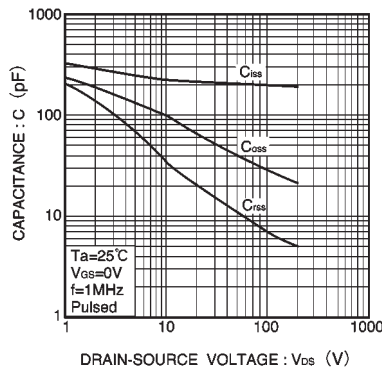


Fig.11 Typical capacitance vs. drain-source voltage

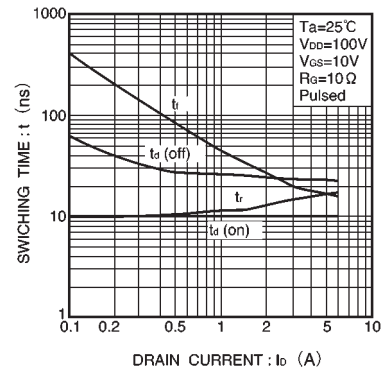


Fig.12 Switching characteristics ( See Figures 16 and 17 for the measurement circuit and resultant waveforms )

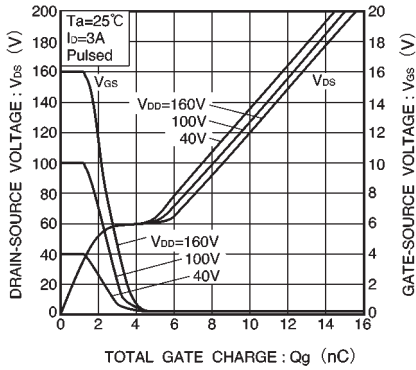


Fig.13 Dynamic input characteristics (See Figure 18 for measurement circuit)

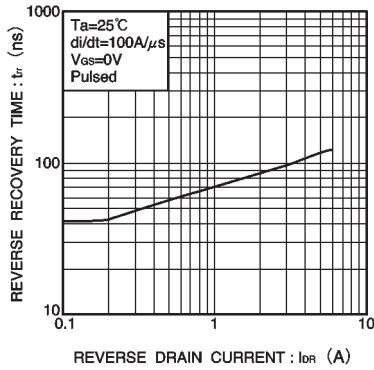


Fig.14 Reverse recovery time vs. reverse drain current

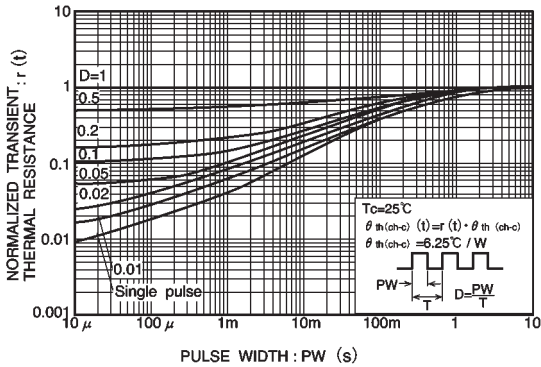


Fig.15 Normalized transient thermal resistance vs. pulse width

● Switching characteristics measurement circuit

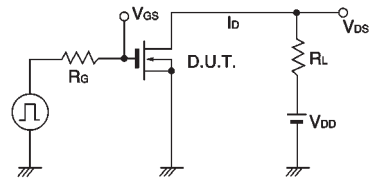


Fig.16 Switching time measurement circuit

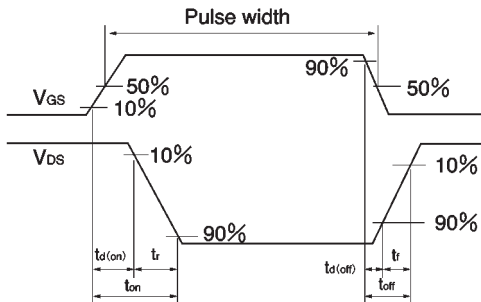


Fig.17 Switching time waveforms

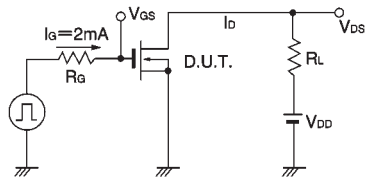


Fig.18 Gate charge time measurement circuit

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